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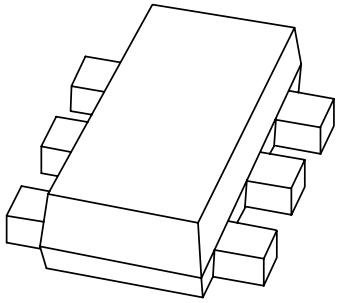
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Kind regards,

Team Nexperia

DATA SHEET



PMEG2015EV

Low V_F MEGA Schottky barrier diode

Product data sheet
Supersedes data of 2003 May 21

2003 Jun 03

NXP founded by Philips

Low V_F MEGA Schottky barrier diode PMEG2015EV

FEATURES

- Forward current: 1.5 A
- Reverse voltage: 20 V
- Very low forward voltage
- Ultra small plastic SMD package
- Flat leads: excellent coplanarity and improved thermal behaviour.

APPLICATIONS

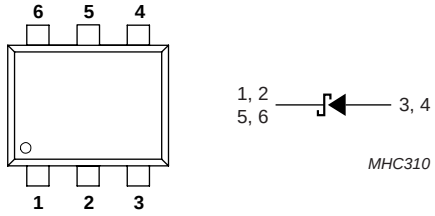
- Low voltage rectification
- High efficiency DC-DC conversion
- Switch mode power supply
- Inverse polarity protection
- Low power consumption applications.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection, encapsulated in a SOT666 ultra small SMD plastic package.

PINNING

PIN	DESCRIPTION
1	cathode
2	cathode
3	anode
4	anode
5	cathode
6	cathode



Marking code: F5.

Fig.1 Simplified outline (SOT666 and symbol).

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage		–	20	V
I_F	continuous forward current	T_s < 55 °C	–	1.5	A
I_{FSM}	non-repetitive peak forward current	t_p = 8 ms square wave; note 1	–	10	A
I_{FRM}	repetitive peak forward current	t_p = 1 ms; δ = ≤ 0.25	–	4.5	A
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		−65	+125	°C

Note

1. Only valid if pins 3 and 4 are connected in parallel.

ELECTRICAL CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_F	continuous forward voltage	see Fig.2; note 1			
		I_F = 10 mA	240	270	mV
		I_F = 100 mA	300	350	mV
		I_F = 1000 mA	480	550	mV
		I_F = 1500 mA	530	660	mV
I_R	continuous reverse current	see Fig.3; note 2			
		V_R = 5 V	5	10	μA
		V_R = 8 V	7	20	μA
		V_R = 15 V	10	50	μA
C_d	diode capacitance	V_R = 5 V; f = 1 MHz; see Fig.4	19	25	pF

Notes

1. Only valid if pins 1, 2 and 5, 6 are soldered on 1 cm^2 copper solder land.
2. Pulse test: t_p = 300 μs; δ = 0.02.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	405	K/W
		note 2	215	K/W
$R_{th\ j\text{-}s}$	thermal resistance from junction to solder point	note 3	80	K/W

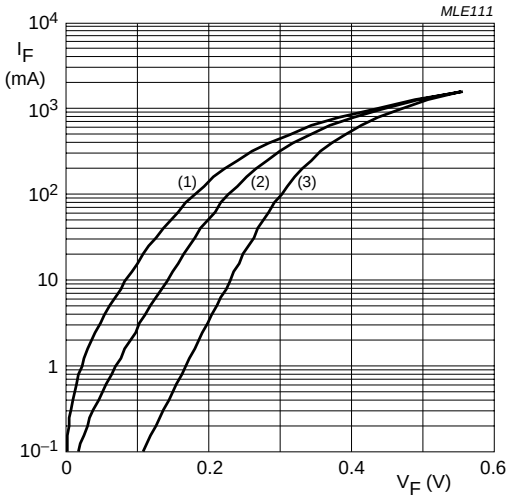
Notes

1. Refer to SOT666 standard mounting conditions.
2. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for cathode 1 cm^2.
3. Soldering point of cathode tabs.

Soldering

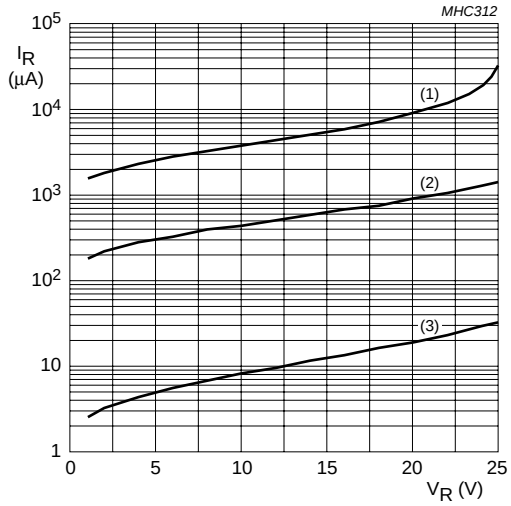
Reflow soldering is the only recommended soldering method.

GRAPHICAL DATA



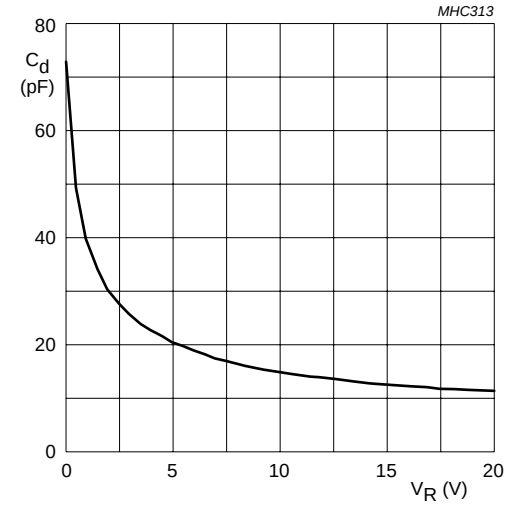
(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.

Fig.2 Forward current as a function of forward voltage; typical values.



(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.

Fig.3 Reverse current as a function of reverse voltage; typical values.

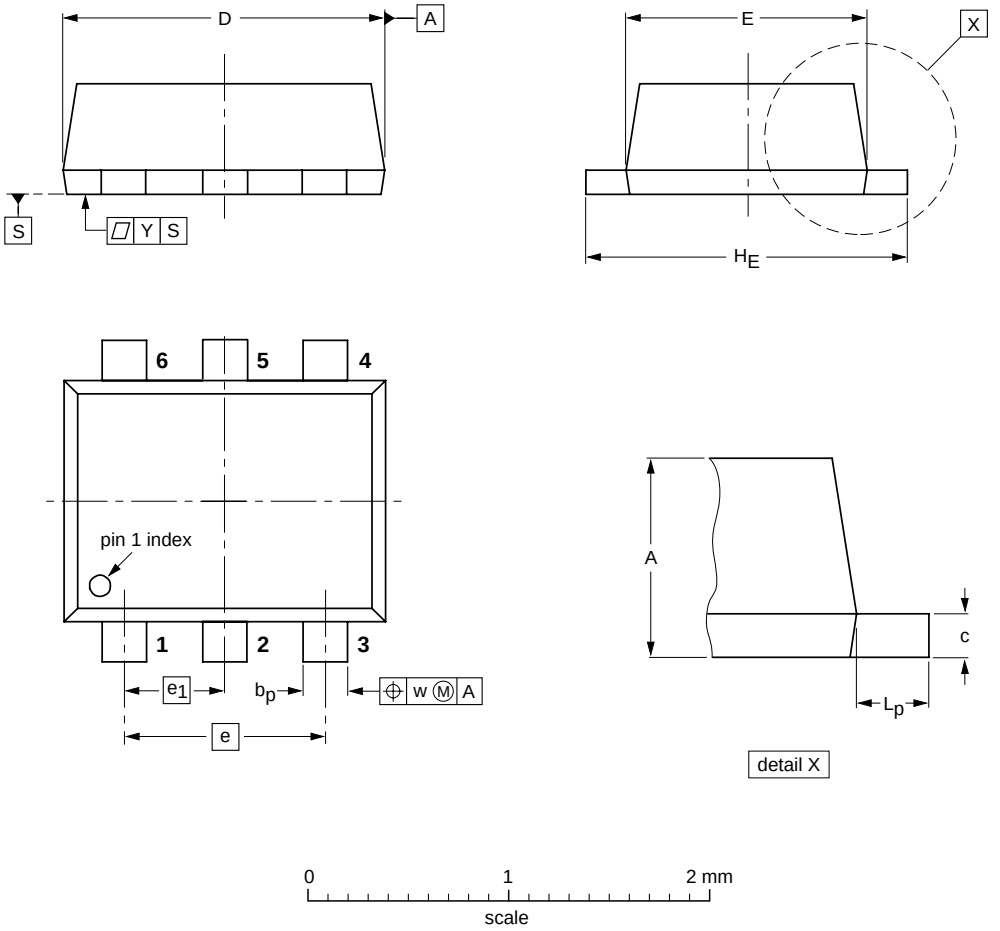


f = 1 MHz; T_{amb} = 25 °C.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads **SOT666**



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_p	c	D	E	e	e_1	H_E	L_p	w	y
mm	0.6 0.5	0.27 0.17	0.18 0.08	1.7 1.5	1.3 1.1	1.0	0.5	1.7 1.5	0.3 0.1	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT666						~~01-01-04~~ 01-08-27

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

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Contact information

For additional information please visit: **http://www.nxp.com**
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